

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
10 April 2003 (10.04.2003)

PCT

(10) International Publication Number
WO 03/030253 A2

(51) International Patent Classification⁷: **H01L 21/8246**,
27/105

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(21) International Application Number: PCT/US02/30784

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3453 (US).

(22) International Filing Date:
27 September 2002 (27.09.2002)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/968,465 1 October 2001 (01.10.2001) US

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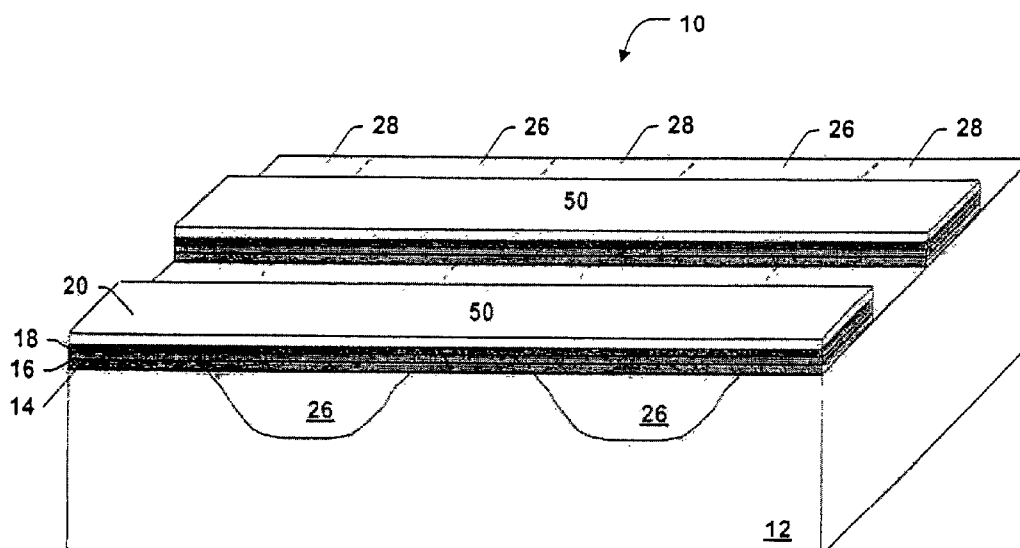
(81) Designated States (*national*): AE, AG, AL, AM, AT, AU,
AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU,
CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH,
GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW,
MX, MZ, NO, NZ, PH, PL, PT, RO, RU, SD, SE, SG, SI,
SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA,
ZW.

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(84) Designated States (*regional*): ARIPO patent (GH, GM,
KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW),
Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE,
ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, SK,
TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

[Continued on next page]

(54) Title: SALICIDED GATE FOR VIRTUAL GROUND ARRAYS



(57) Abstract: Processes for doping and saliciding word lines (20) in a virtual ground array flash memory device without causing shorting between bit lines (26) are disclosed. According to one aspect, word lines (20) are doped prior to patterning the poly layer from which the word lines (20) are formed in the core region. Thereby, the poly layer protects the substrate between the word lines (20) from doping that could cause shorting between bit lines (26). According to another aspect, word lines (20) are exposed while spacer material, dielectric, or like material protects the substrate between word lines (20). The spacer material or dielectric prevents the substrate from becoming salicided in a manner that, like doping, could cause shorting between bit lines (26). Disclosed are virtual ground array flash memory devices with doped and salicided word lines (20), but no shorting between bit lines (26) even in virtual ground arrays where there are no oxide island isolation regions (28) between bit lines (26).



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Published:

— without international search report and to be republished upon receipt of that report

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